2SB1054

Silicon PNP triple diffusion planar type

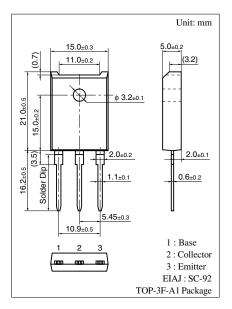
For high power amplification Complementary to 2SD1485

■ Features

- \bullet Excellent current I_C characteristics of forward current transfer ratio $h_{FE}\ vs.\ collector$
- Wide area of safe operation (ASO)
- High transition frequency f_T
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25$ °C

| Parameter | | Symbol | Rating | Unit |
|------------------------------|---------------------|-----------------|-------------|------|
| Collector to base voltage | | V_{CBO} | -100 | V |
| Collector to emitter voltage | | V_{CEO} | -100 | V |
| Emitter to base voltage | | V_{EBO} | -5 | V |
| Peak collector current | | I _{CP} | -8 | A |
| Collector current | | I_C | -5 | A |
| Collector power | $T_C = 25^{\circ}C$ | P_{C} | 60 | W |
| dissipation | $T_a = 25^{\circ}C$ | | 3 | |
| Junction temperature | | T _j | 150 | °C |
| Storage temperature | | T_{stg} | -55 to +150 | °C |



■ Electrical Characteristics $T_C = 25$ °C

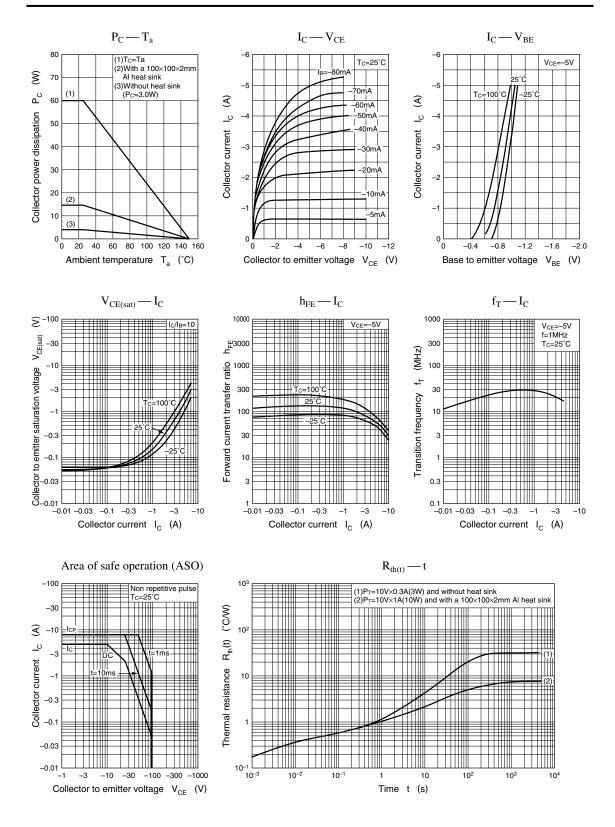
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|---|----------------------|--|-----|-----|-------|------|
| Collector cutoff current | I_{CBO} | $V_{CB} = -100 \text{ V}, I_E = 0$ | | | -50 | μΑ |
| Emitter cutoff current | I_{EBO} | $V_{EB} = -3 \text{ V}, I_C = 0$ | | | -50 | μΑ |
| Forward current transfer ratio | h _{FE1} | $V_{CE} = -5 \text{ V}, I_{C} = -20 \text{ mA}$ | 20 | | | |
| | h _{FE2} * | $V_{CE} = -5 \text{ V}, I_{C} = -1 \text{ A}$ | 60 | | 200 | |
| | h_{FE3} | $V_{CE} = -5 \text{ V}, I_{C} = -3 \text{ A}$ | 20 | | | |
| Base to emitter voltage | V_{BE} | $V_{CE} = -5 \text{ V}, I_{C} = -3 \text{ A}$ | | | -1.8 | V |
| Collector to emitter saturation voltage | V _{CE(sat)} | $I_C = -3 \text{ A}, I_B = -0.3 \text{ A}$ | | | - 0.2 | V |
| Transition frequency | f_T | $V_{CE} = -5 \text{ V}, I_C = -0.5 \text{ A}, f = 1 \text{ MHz}$ | | 20 | | MHz |
| Collector output capacitance | C_{ob} | $V_{CB} = -10 \text{ V}, f = 1 \text{ MHz}$ | | 170 | | pF |

Note) *: Rank classification

| Rank | Q | Р | | | |
|------------------|-----------|------------|--|--|--|
| h _{FE2} | 60 to 120 | 100 to 200 | | | |

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Power Transistors 2SB1054



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